NPN SILICON RF MICROWAVE TRANSISTOR

DESCRIPTION:

The **ASI SD1485-1** is Designed for Television Band III Applications up to 230 MHz.

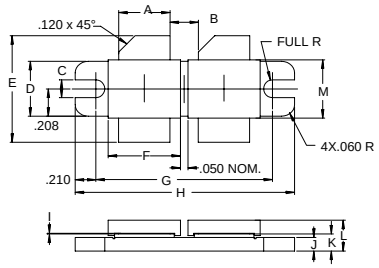
FEATURES:

- Common Emitter
- P_G = 11 dB at 100 W/225 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	25 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	3.0 V
P_{DISS}	385 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.45 °C/W

PACKAGE STYLE .450 BAL FLG (B)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.373 / 9.47	.385 / 9.78
B	.205 / 5.21	
C	.120 / 3.25	.130 / 3.30
D	.411 / 10.44	.421 / 10.69
E	.825 / 20.96	.865 / 21.97
F	.525 / 13.34	.535 / 13.59
G	1.255 / 31.88	1.265 / 32.18
H	1.675 / 42.55	1.685 / 42.80
I	.002 / 0.05	.006 / 0.15
J	.095 / 2.41	.105 / 2.67
K	.115 / 2.92	.135 / 3.43
L		.250 / 6.35
M	.445 / 11.30	.457 / 11.61

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 100 mA	65			V
BV_{CER}	I_C = 100 mA R_{BE} = 15 Ω	60			V
BV_{CEO}	I_C = 100 mA	35			V
BV_{EBO}	I_E = 20 mA	3.0			V
I_{CES}	V_{CB} = 32 V			10	mA
h_{FE}	V_{CE} = 5.0 V I_C = 4.0 A	20		70	---
C_{OB}	V_{CB} = 28 V f = 1.0 MHz	---	130	---	pF
P_G	V_{CE} = 32 V I_C = 2 X 500 mA f = 230 MHz	11			dB
η_C	P_{OUT} = 200 W	50			%

Specifications are subject to change without notice.